



General Description

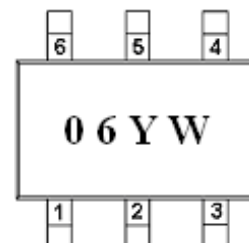
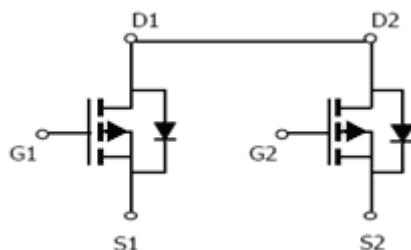
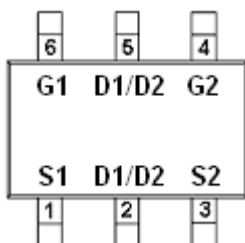
AFP8206, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- -20V/-4.5A, $R_{DS(ON)}=56m\Omega@V_{GS}=4.5V$
- -20V/-3.2A, $R_{DS(ON)}=70m\Omega@V_{GS}=2.5V$
- -20V/-2.8A, $R_{DS(ON)}=96m\Omega@V_{GS}=1.8V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TSOP-6 package design

Pin Description (TSOP-6)



Application

- Load Switch
- Portable Equipment
- Battery Powered System

Pin Define

Pin	Symbol	Description
1	S1	Source
2	D1/D2	Drain
3	S2	Source
4	G2	Gate
5	D1/D2	Drain
6	G1	Source

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP8206TS6RG	06YW	TSOP-6	Tape & Reel	3000 EA

- ※ 06 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFP8206TS6RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

($T_A=25^\circ\text{C}$ Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate –Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current($T_J=150^\circ\text{C}$)	I_D	$T_A=25^\circ\text{C}$	-4.5
		$T_A=70^\circ\text{C}$	2.8
Pulsed Drain Current	I_{DM}	-15	A
Continuous Source Current(Diode Conduction)	I_S	-1.6	A
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	2.0
		$T_A=70^\circ\text{C}$	1.3
Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55/150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ\text{C/W}$

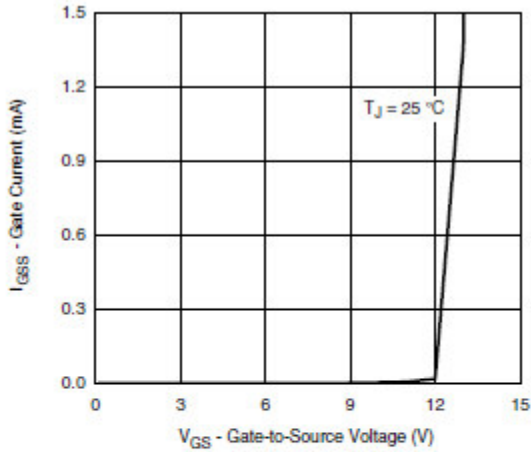
Electrical Characteristics

($T_A=25^\circ\text{C}$ Unless otherwise noted)

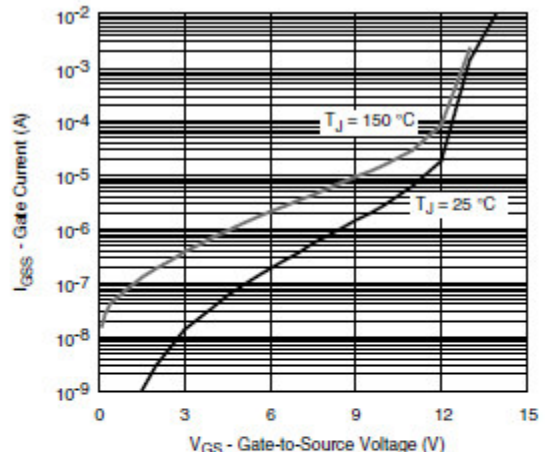
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu\text{A}$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.4		-0.8	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-16V, V_{GS}=0V$			-1	uA
		$V_{DS}=-16V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			-10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq -5V, V_{GS}=-4.5V$	-6			A
		$V_{DS} \geq -5V, V_{GS}=-2.5V$	-4			
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=4.5A$		50	56	m Ω
		$V_{GS}=-2.5V, I_D=-3.2A$		60	70	
		$V_{GS}=-1.8V, I_D=-2.8A$		80	96	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-3.6A$		10		S
Diode Forward Voltage	V_{SD}	$I_S=-1.6A, V_{GS}=0V$		-0.85	-1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-4.5V$ $I_D \equiv -4.0A$		8.0	12	nC
Gate-Source Charge	Q_{gs}			0.9		
Gate-Drain Charge	Q_{gd}			3.0		
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V$ $f=1\text{MHz}$		780		pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			55		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=2.3\Omega$ $I_D \equiv -4.0A, V_{GEN}=-4.5V$ $R_G=1\Omega$		0.2	0.3	us
	t_r			1.0	1.5	
Turn-Off Time	$t_{d(off)}$			4.0	6.0	
	t_f			2.0	3.0	



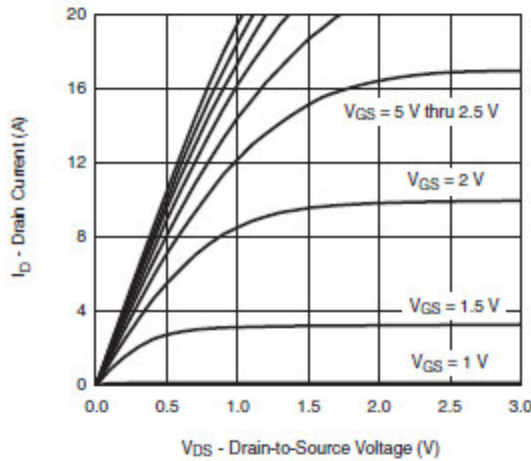
Typical Characteristics



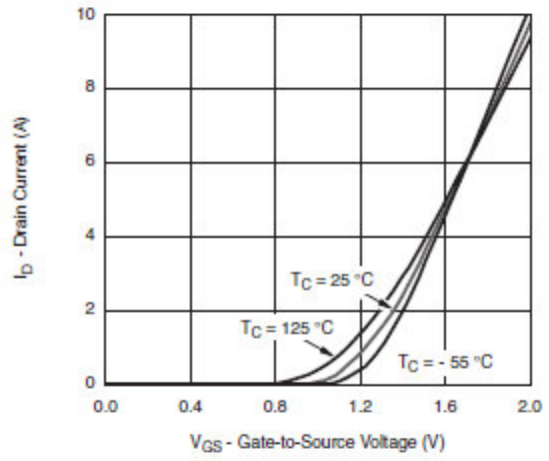
Gate Current vs. Gate-Source Voltage



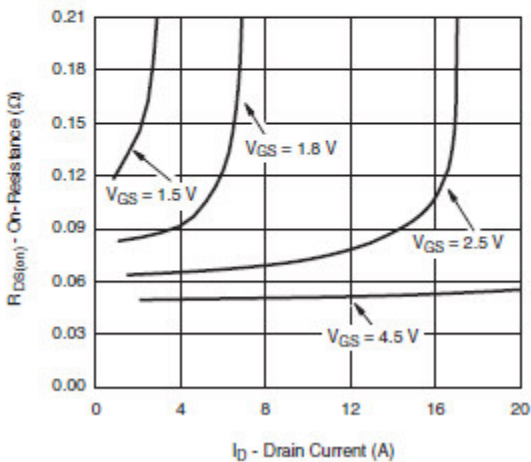
Gate Current vs. Gate-Source Voltage



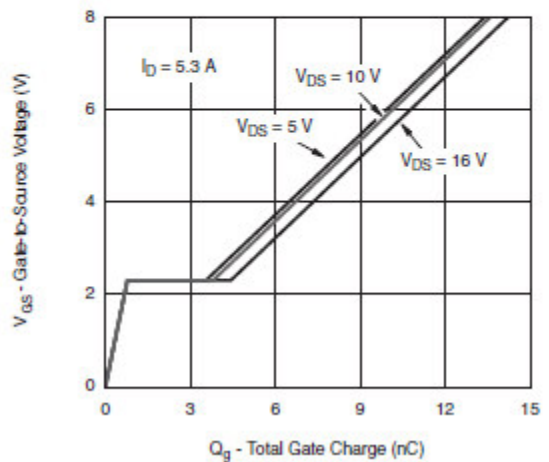
Output Characteristics



Transfer Characteristics



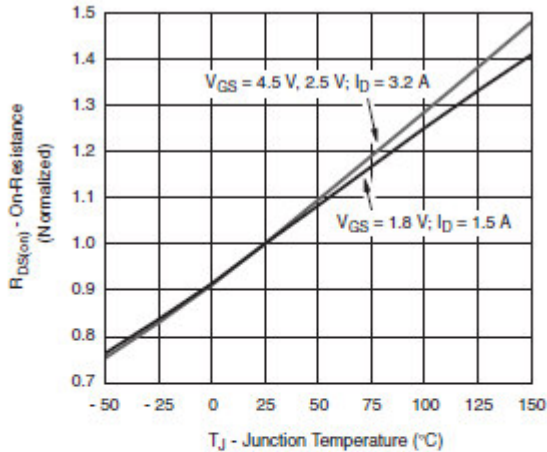
On-Resistance vs. Drain Current



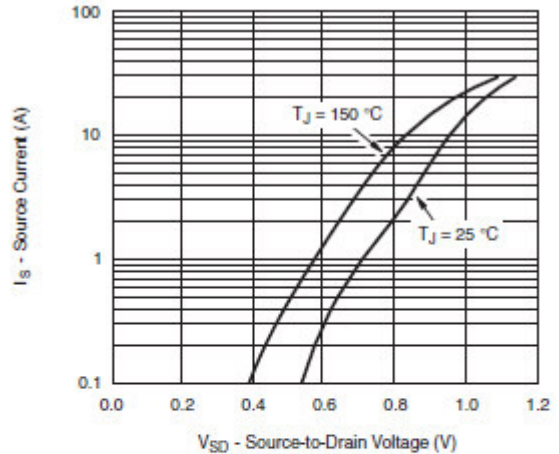
Gate Charge



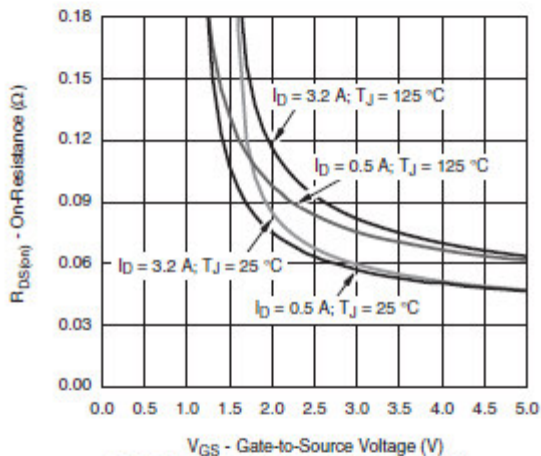
Typical Characteristics



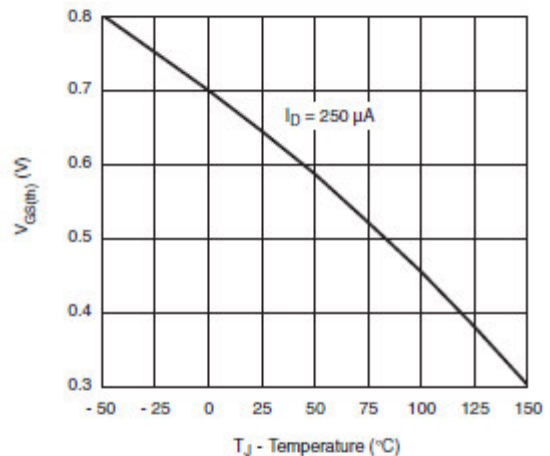
On-Resistance vs. Junction Temperature



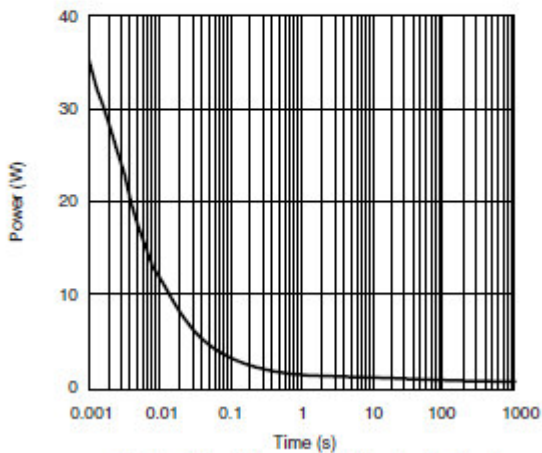
Source-Drain Diode Forward Voltage



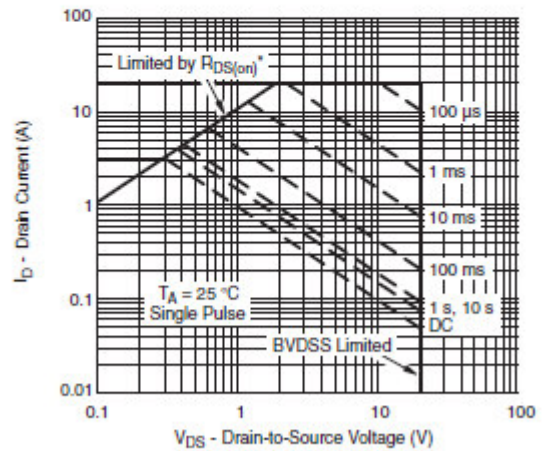
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

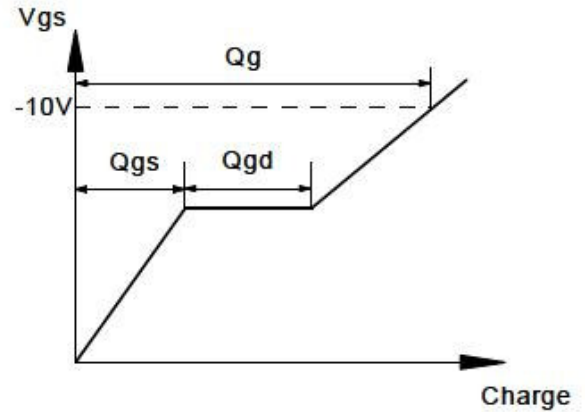
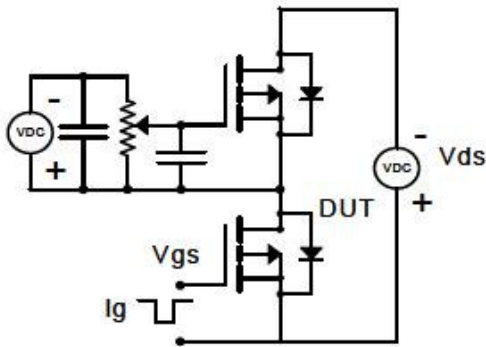


Safe Operating Area, Junction-to-Ambient
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

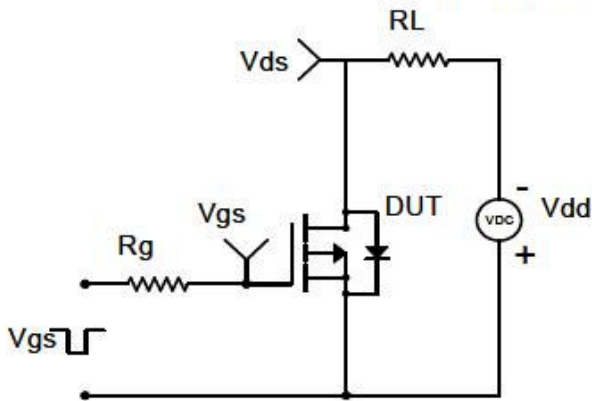


Typical Characteristics

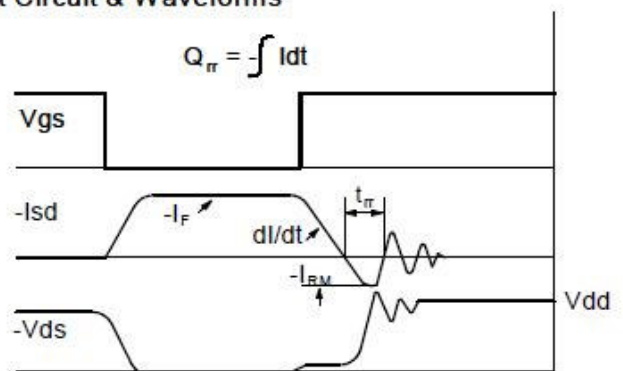
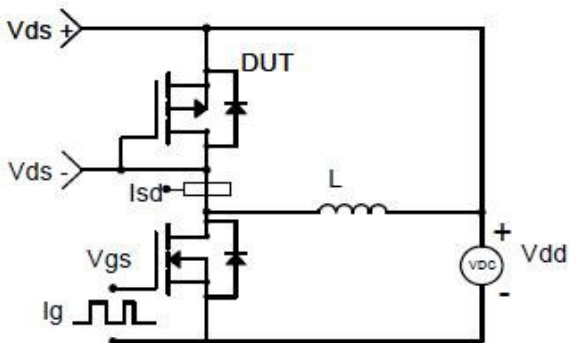
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

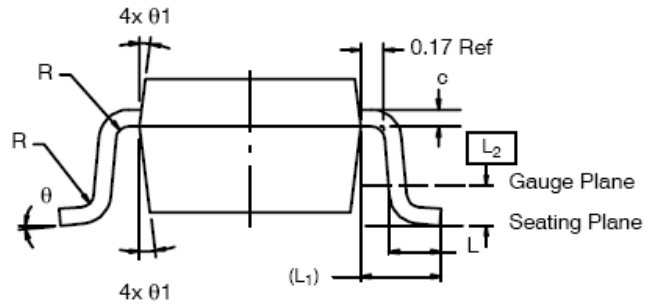
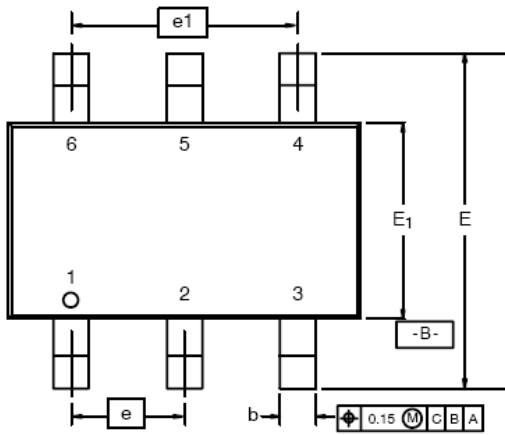


Diode Recovery Test Circuit & Waveforms





Package Information (TSOP-6)



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.96	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
e ₁	1.90	2.00	2.10	0.075	0.080	0.085
L	0.35	-	0.50	0.014	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		

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